

L Number	Hits	Search Text	DB	Time stamp
1	2792480	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 12:59
2	56	(memory or storage) and (precharg\$5 or pre-charge\$5 or charge\$5) near3 (bit or bitline) and programmable with (resistor or resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 13:02
3	37	((memory or storage) and (precharg\$5 or pre-charge\$5 or charge\$5) near3 (bit or bitline) and programmable with (resistor or resistance)) and transistor with cell	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/21 13:03